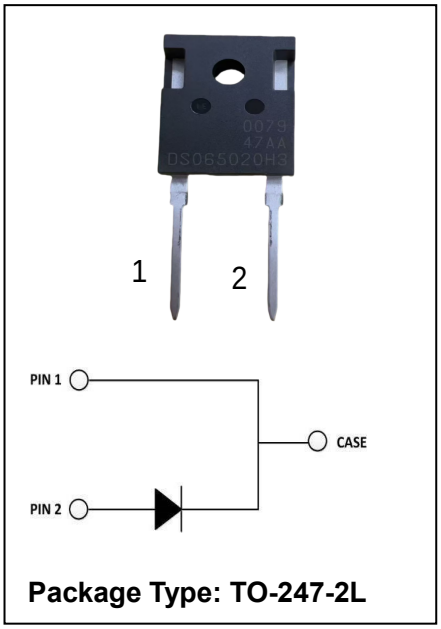
Features

- Revolutionary semiconductor material - Silicon Carbide (SiC)
- No reverse recovery
- High-speed switching performance
- Temperature-independent switching behavior
- System cost / size savings due to reduced cooling requirements
- Junction temperature range from -55℃ to 175℃
- RoHS compliant



Package Type: TO-247-2L

Potential Applications

- Industrial power supplies: Industrial UPS
- Battery chargers
- Solar inverters
- Switch mode power supplies

Description

The TKDS065J020H3 SiC Schottky Barrier Diode (SBD) features with the highest performance and reliability. It registers higher efficiency, higher operation temperature and lower loss and can be operated at higher frequency than Si-based solutions. As to the Schottky structure, it shows no recovery at turn-off and allows a low leakage current with reverse voltage up to 650V. It can contribute to system miniaturization and achieve lightweight system design. Using RoHS compliant components, it is qualified for use in industrial application.

Product Specifications

Device	V_{RRM}	I_F (135℃)	V_F (25℃)	Q_C	Marking
TKDS065J020H3	650V	25A	1.35V	55nC	DS065020H3

Maximum Ratings

(Tc = 25℃, unless otherwise specified)

Parameter	Symbol	Value	Unit	Test conditions
Repetitive peak reverse voltage	V_{RRM}	650	V	T_C = 25℃
Surge peak reverse voltage	V_{RSM}	650		T_C = 25℃
DC reverse voltage	V_{DC}	650		T_C = 25℃
Continuous forward current	I_F	51	A	T_C = 25℃
		25		T_C = 135℃
		20		T_C = 150℃
Surge non-repetitive forward current	I_{FSM}	140	A	T_C = 25℃, t_p = 10ms, half sine pulse
Surge repetitive forward current	I_{FRM}	96	A	T_C = 25℃, t_p = 10ms, half sine wave D = 0.1
Power dissipation	P_{tot}	178	W	T_C = 25℃
i^2t value	$\int i^2dt$	98	A^2s	T_C = 25℃, t_p = 10ms
Operating junction temperature	T_j	-55~175	℃	
Storage temperature	T_{stg}	-55~175	℃	
Mounting torque	M	1	Nm	M3 screw

Thermal Resistance

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Thermal resistance from junction to case	$R_{th(j-c)}$	/	0.84	/	℃/W	

Static Electrical Characteristics

(T_j = 25℃, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
DC blocking voltage	V_{DC}	650	/	/	V	I_R = 100 μA
Forward voltage	V_F	/	1.35	1.50	V	I_F = 20A, T_j = 25℃
		/	1.70	1.90		I_F = 20A, T_j = 175℃
Reverse current	I_R	/	2	40	μA	V_R = 650V, T_j = 25℃
		/	10	100		V_R = 650V, T_j = 175℃

Dynamic Electrical Characteristics

(T_j = 25℃, unless otherwise specified)

Parameter	Symbol	Values			Unit	Test conditions
		Min.	Typ.	Max.		
Total capacitance	C	/	1018	/	pF	V_R = 0V, f = 1MHz
		/	104	/		V_R = 200V, f = 1MHz
		/	89	/		V_R = 400V, f = 1MHz
Total capacitive charge	Q_C	/	55	/	nC	V_R = 400V
Capacitance stored energy	E_C	/	8.3	/	μJ	V_R = 400V

Electrical Characteristic Diagrams

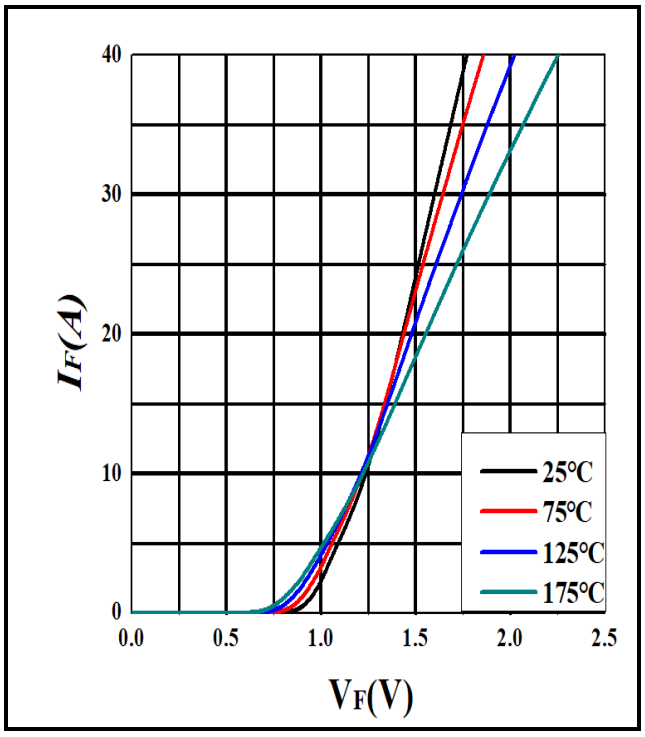


Figure 1. Forward characteristics

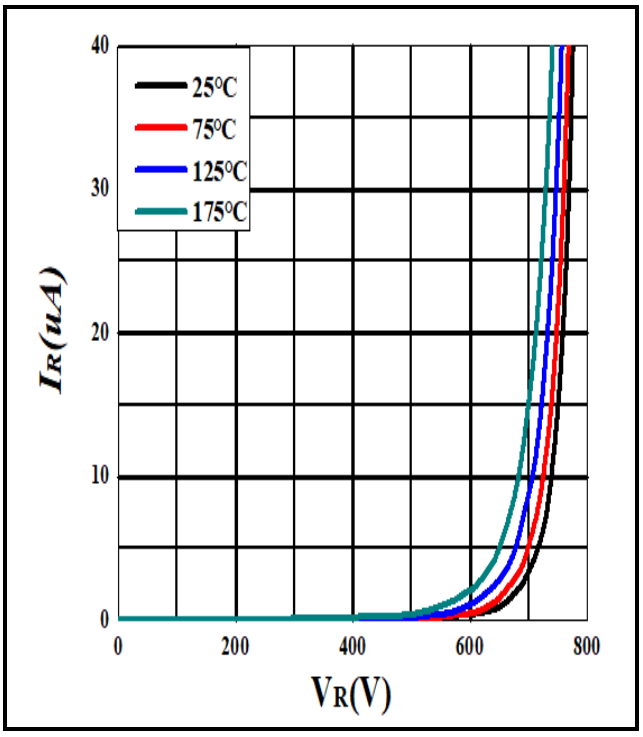


Figure 2. Reverse characteristics

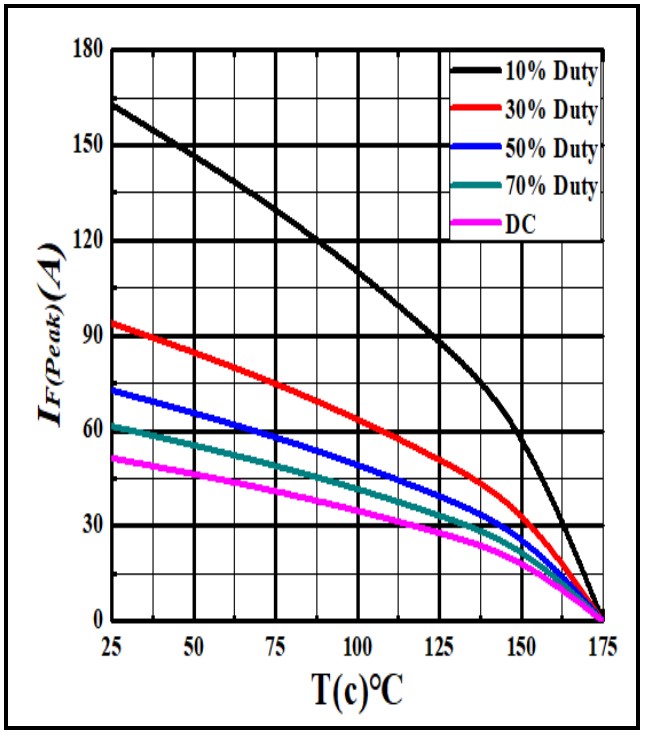


Figure 3. Current derating

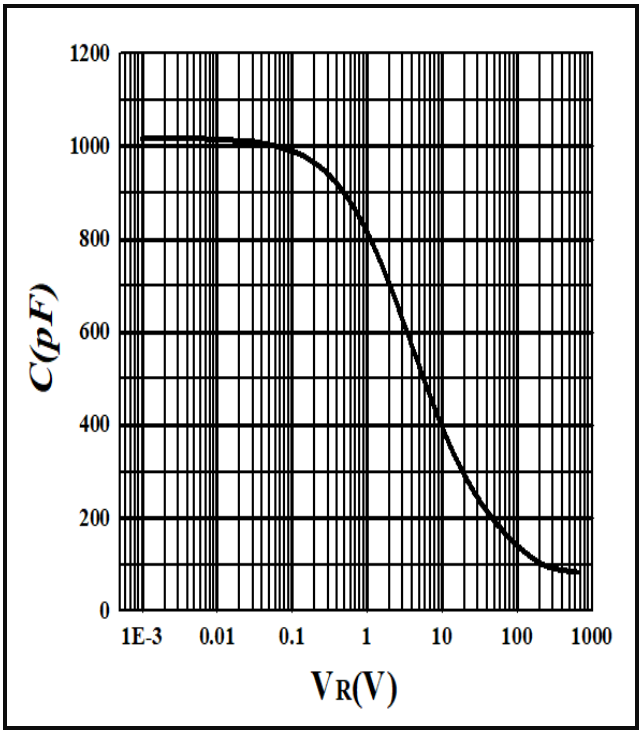


Figure 4. Capacitance vs. reverse voltage

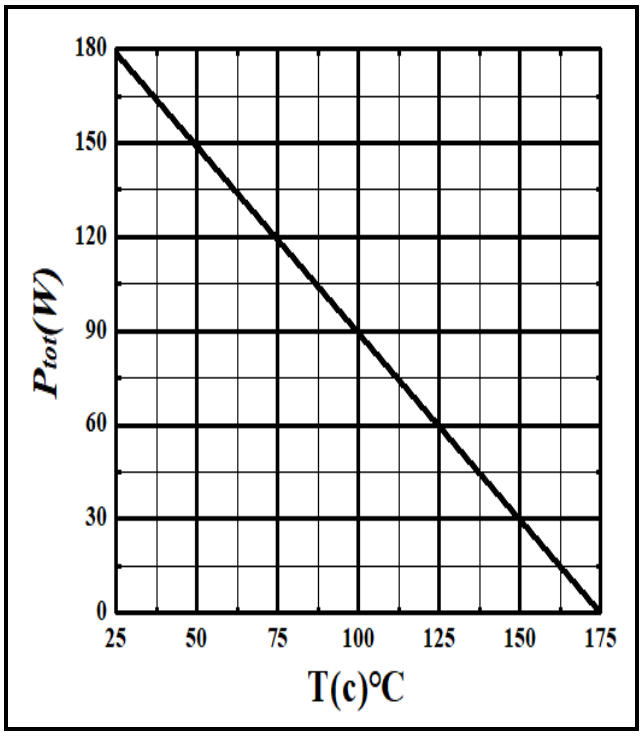


Figure 5. Power derating

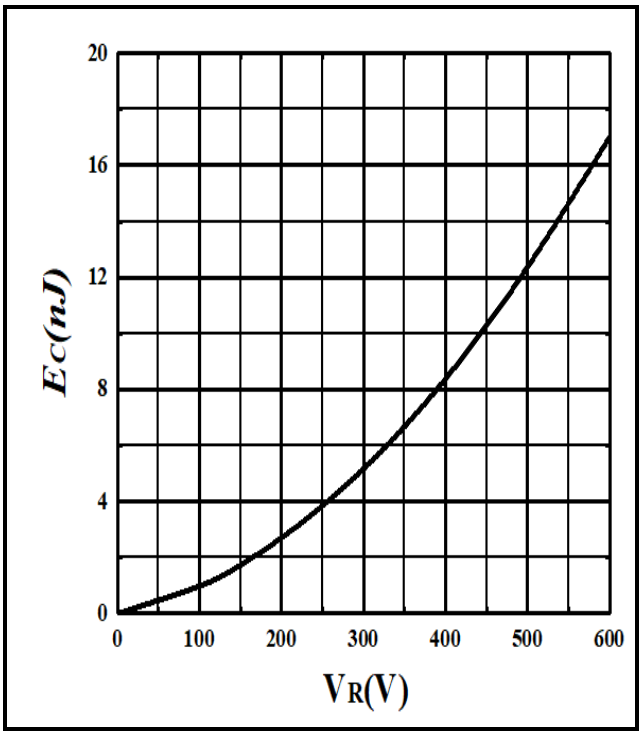


Figure 6. Capacitance stored energy

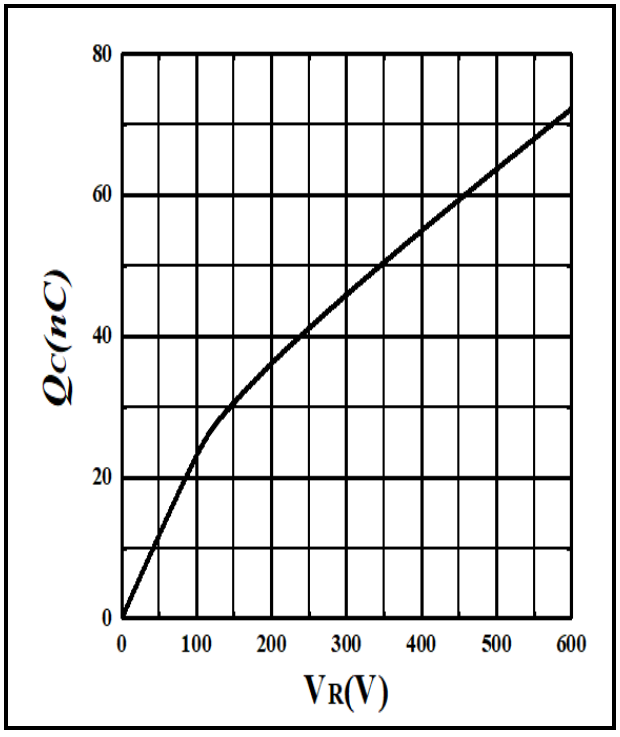
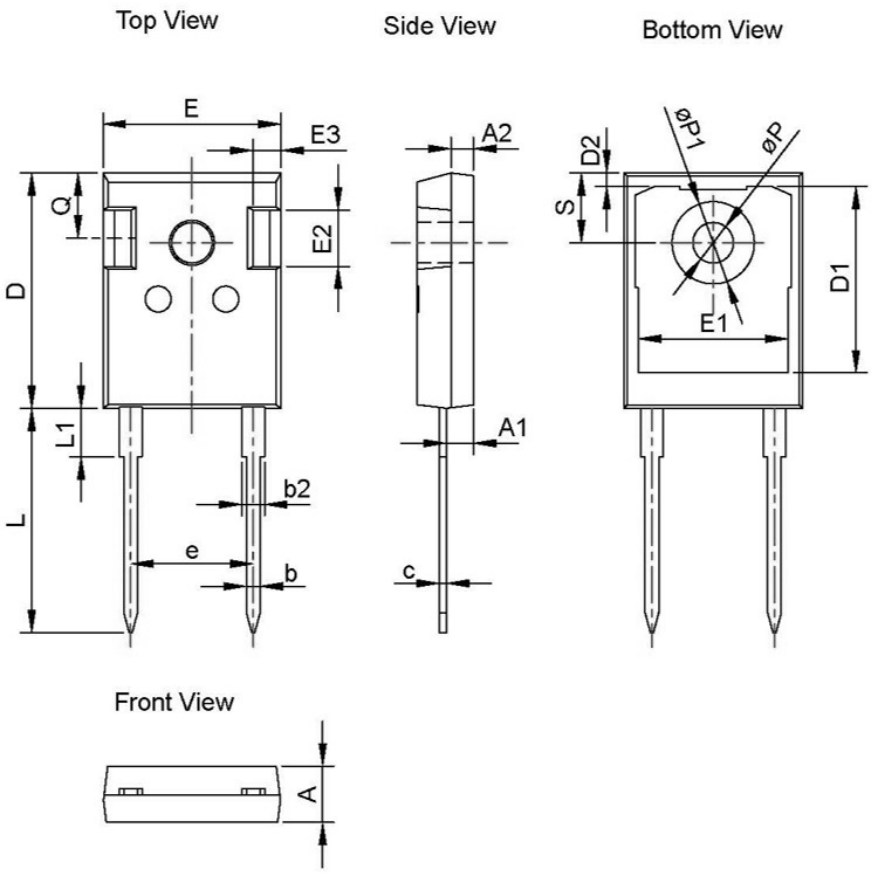


Figure 7. Total capacitance charge vs. reverse voltage

Package Information



Dimension unit: [mm]			
Symbol	Min	Nom	Max
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.85	2.00	2.15
b	1.11	1.21	1.36
b2	1.91	2.01	2.21
c	0.51	0.60	0.75
D	20.70	21.00	21.30
D1	16.25	16.55	16.85
D2	1.00	1.20	1.35
E	15.50	15.80	16.10
E1	13.00	13.30	13.60
E2	4.80	5.00	5.20
E3	2.30	2.50	2.70
e	10.88 BSC		
L	19.62	19.92	20.22
L1	-	-	4.30
øP	3.40	3.60	3.80
øP1	-	-	7.30
Q	5.40	5.80	6.20
S	6.20 BSC		